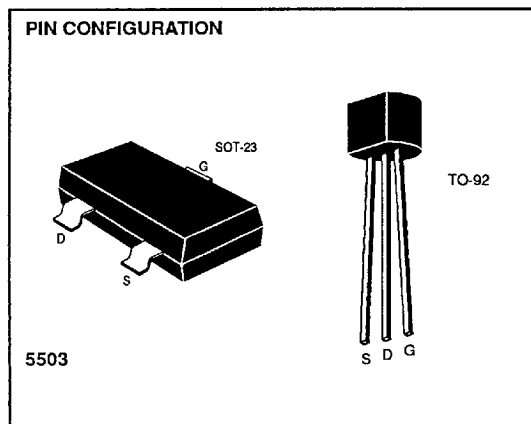


2N5460 – 2N5465 / SST5460 – SST5465



PRODUCT MARKING (SOT-23)			
P/N	MARK	P/N	MARK
SST5460	SO0	SST5463	SO3
SST5461	SO1	SST5464	SO4
SST5462	SO2	SST5465	SO5

ABSOLUTE MAXIMUM RATINGS

(T_A = 25°C unless otherwise specified)

Drain-Gate or Source-Gate Voltage	
2N5460 - 2N5462	-40V
2N5463 - 2N5465	-60V
Gate Current	10mA
Storage Temperature Range	-65°C to +150°C
Operating Temperature Range	-55°C to +135°C
Lead Temperature (Soldering, 10sec)	+300°C
Power Dissipation	310mW
Derate above 25°C	2.82mW/°C

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ORDERING INFORMATION

Part	Package	Temperature Range
2N5460-65	Plastic TO-92	-55°C to +135°C
SST5461-65	Plastic SOT-23	-55°C to +135°C
X2N5461-65	Sorted Chips in Carriers	-55°C to +135°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
BV _{GSS}	Gate-Source Breakdown Voltage	5460, 5461, 5462 5463, 5464, 5465	40 60	V	I _G = 10μA, V _{DS} = 0
V _{GS(off)}	Gate-Source Cutoff Voltage	5460, 5463 5461, 5464 5462, 5465	0.75 1.0 1.8	6.0 7.5 9.0	V _{DS} = -15V, I _D = 1.0μA
I _{GSS}	Gate Reverse Current	5460, 5461, 5462 5463, 5464, 5465 5460, 5461, 5462 5463, 5464, 5465	5.0 5.0 1.0 1.0	nA μA	V _{DS} = 0 T _A = 100°C
I _{DSS}	Zero-Gate Voltage Drain Current	5460, 5463 5461, 5464 5462, 5465	-1.0 -2.0 -4.0	-5.0 -9.0 -16	mA V _{GS} = 0 V _{DS} = -15V
V _{GS}	Gate-Source Voltage	5460, 5463 5461, 5464 5462, 5465	0.5 0.8 1.5	4.0 4.5 6.0	V I _D = 0.1mA I _D = -0.2mA I _D = -0.4mA

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2N5460 – 2N5465 / SST5460 – SST5465



ELECTRICAL CHARACTERISTICS (Continued) ($T_A = 25^\circ\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS	
g_{fs}	Forward Transadmittance	2N5460, 2N5463	1000	4000	μS	$f = 1.0\text{kHz}$
		2N5461, 2N5464	1500	5000		
		2N5462, 2N5465	2000	6000		
g_{os}	Output Admittance		75	μS	$V_{DS} = 15\text{V}$ $V_{GS} = 0\text{V}$	$f = 1\text{mHz}$
C_{iss}	Input Capacitance (Note 1)		7	pF		
C_{rss}	Reverse Transfer Capacitance (Note 1)		2.0	pF		
NF	Common-Source Noise Figure (Note 1)		2.5	dB		$f = 100\text{Hz}$ $\text{BW} = 1.0\text{Hz}$
\bar{e}_n	Equivalent Short-Circuit Input Noise Voltage (Note 1)		115	$\frac{\text{nV}}{\sqrt{\text{Hz}}}$		$R_G = 1.0\text{M}\Omega$

NOTE 1: For design reference only, not 100% tested.

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